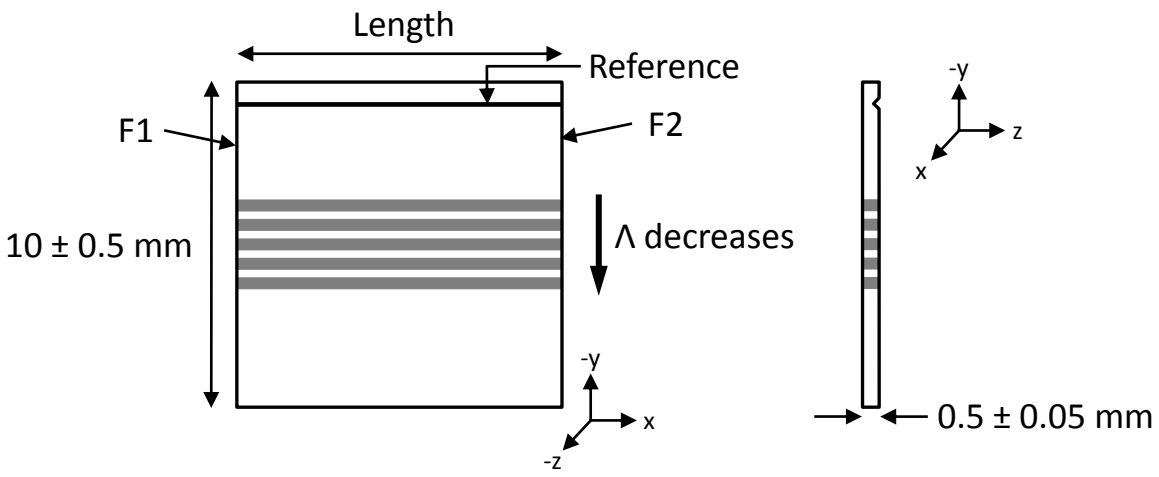
Device Specification

MDFG1-0.5-xx



[Image for reference only. Not to scale.]

Description	MgO doped PPLN DFG crystal for 1064nm and 737-786nm
Thickness(z)	0.5mm± 0.05mm
Width(y)	10mm±0.5mm
Length(x)	40mm±0.5mm or 20mm±0.5mm
Periods(Λ)	18.50, 18.80, 19.10, 19.40, 19.70, 20.00, 20.30, 20.60, 20.90µm

NOTES:

1 The DFG device material is Magnesium doped Lithium Niobate with nine periodically poled gratings. Each grating is 0.5mm wide with individual periods as listed above. A saw-cut reference mark is provided on the +z face of the crystal to determine the largest grating period (see above diagram). Each poled grating is separated by 0.2mm wide regions of unpoled material.

2 The average mark-to-space ratio of each grating is better than 70:30.

3 Each device is etched to make the poled gratings visible. Due to the wet-etch nature of this process the top and bottom surface finish of each device may appear cloudy or uneven.

4 Perpendicularity of input/output facets F1 and F2 to gratings is within ±0.15°. Parallelism between end facets F1 and F2 is within ±5 minutes.

5 Optical finish of facets F1 and F2 is within 20/10 scratch dig with λ/8@1064nm. No more than two 100µm size chips per end facet.

6 AR coated to R<1.5% @ 700-1100nm for the input facet (F2) and 2.4-4.8µm for the output facet (F1).

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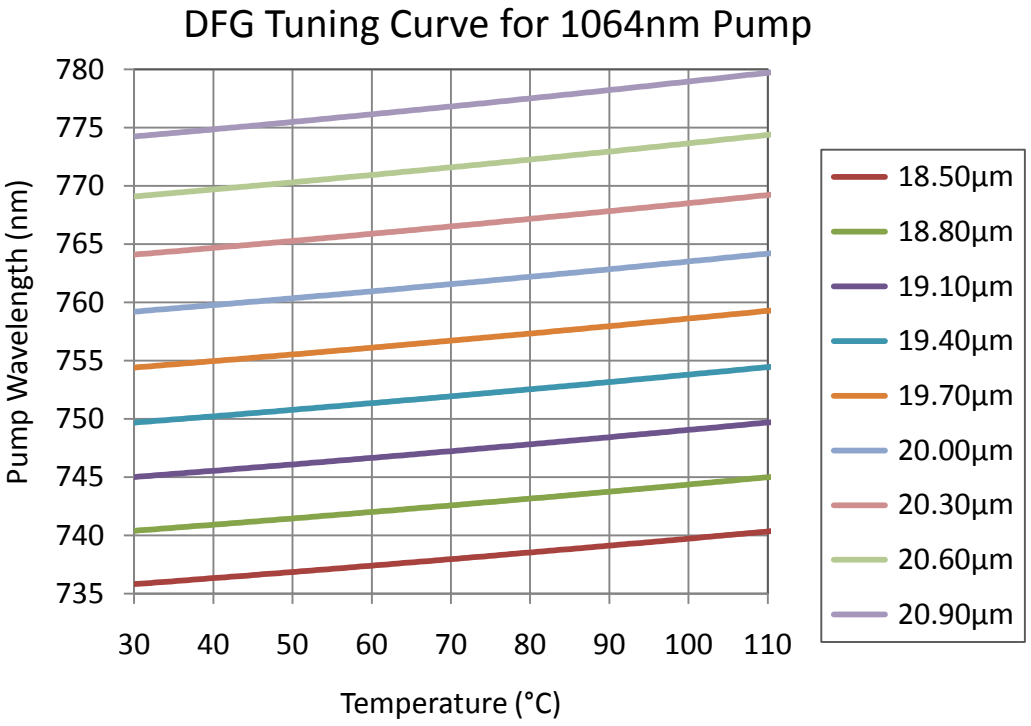

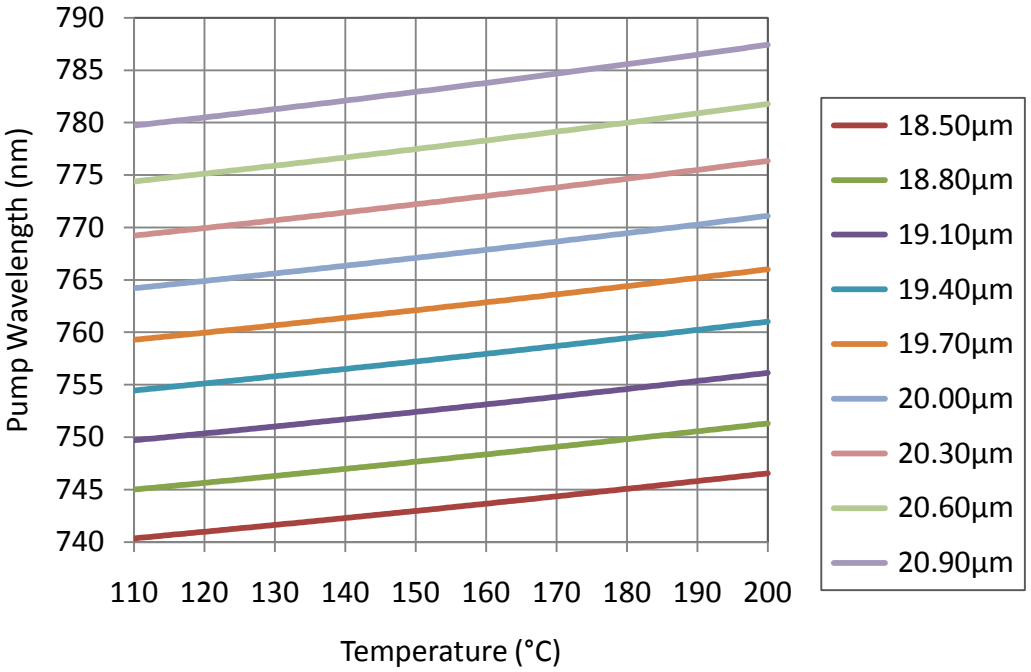

For more information, please contact us at:

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